

PLASTIC SEALED HIGH VOLTAGE SILICON RECTIFIER STACK

Features:

• Silicon Rectification Diode

Application:

• For high voltage rectification for 'MWO of frequency conversion'





MAX.RATED VALUE

| Rated Value | Sign | Condition | R8KH | Unit |
|------------------------------------------------------------------|------------------|---------------------------------------------------------------------------------------------------------------------|----------|----------------|
| Peak Reverse Repetitive Voltage | V _{RRM} | | 8.7 | kV |
| Reverse Surge Current | I _{rsm} | width 1ms triangle wave single pulse | 0.2 | А |
| Average Forward Rectifier Current | Io | | 0.38 | А |
| Max. Irrepetitive Surge current | I _{FSM} | Ta=25 [°] C ["] rated load ["] half cycle ["] single phase ["] 50Hz | 15 | А |
| Iaximum Junction Temperature Tj half cycle sinewave peak voltage | | | 130 | °C |
| Store Temperature | Tstg | | -40~+130 | ⁰ C |

Electric Characteristic

| Rated Value | Sign | Condition | R8KH | Unit |
|--------------------------------------------|-----------------|----------------------------------------------------------|------|------|
| Max Forward Voltage Drop | V | I _F =0.35A | 14 | V |
| Max. Reverse Recovery Time | trr | $I_{\rm F} = I_{\rm R} = 100 {\rm mA} 90\% {\rm Value}.$ | 0.15 | μS |
| Max. Normal Temperature Reverse Current | I _{R1} | V _R =V _{RRM} ″ 25 °C | 5.0 | μA |
| Max. High Temperature Reverse Current | I _{R2} | $V_{R}=V_{RRM}$ " 100 °C | 50 | μA |
| Reverse Breakdown Voltage | V _{br} | I _R =100uA | 8.7 | kV |

RATING AND CHARACTERISTICS CURVES (R8KH)

Fig.1 Insulation resistance test and insulation strength test



Roll metal foil with 3mm width around center of the body

Insulation resistance test condition: Measure between A and B by using a DC 500V insulation resistance tester. Insulation strength test condition: Apply half sine wave voltage with 10KV wave height between A and B in insulation liquid.

Fig2. Derating of forward current for ambient temperature

(On condition of provision of a fin on cathode side and air cooling)





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RATING AND CHARACTERISTICS CURVES (R8KH)

Figure 5. I F(AV) - Ta Derating

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R8KH-H45





PACKAGING OF DIODE AND BRIDGE RECTIFIERS

| PACKAGE | PACKING | BAG | BAG | PER BOX | BOX SIZE | CARTON | PER CARTON |
|---------|---------|------|----------|---------|-------------|-------------|------------|
| | CODE | (EA) | SIZE(mm) | (EA) | (mm) | SIZE(mm) | (EA) |
| R8KH | -B | 100 | 140*135 | 1,000 | 350*130*105 | 555*370*155 | 5,000 |



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